

Silicon NPN Power Transistors

2SD792

DESCRIPTION

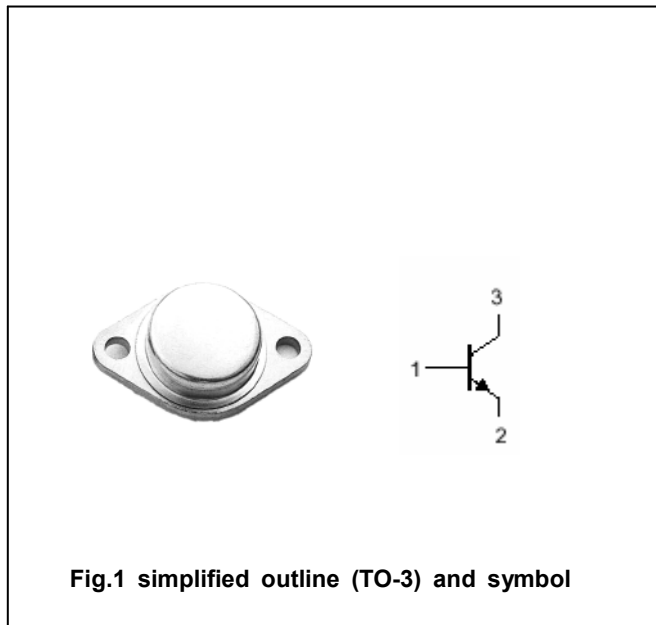
- With TO-3 package
- High voltage
- Wide area of safe operation

APPLICATIONS

- For line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	700	V
V _{EBO}	Emitter-base voltage	Open collector	4	V
I _C	Collector current		5	A
I _{CM}	Collector current-peak		7	A
P _T	Total power dissipation	T _C =90□	35	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0; L=25mH	700			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10mA; I _C =0	4			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5 A; I _B =2 A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5 A; I _B =2 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μA
		V _{CB} =1500V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =4A ; V _{CE} =10V	4		12	
t _f	Fall time	I _C =4A; I _{Bend} =1.8A; L _B =10μH			0.7	μs
t _{stg}	Storage time			13		μs

PACKAGE OUTLINE

